REMARKS

Claims 1, 17 and 18 are amended. Claims 54 and 55 are added. Claims 1-26, 54 and 55 are in the application for consideration.

The specification is amended to correct a typographical error.

Claims 1 and 18 are amended to remove reference to characterization of the deposition chamber within which the processing occurs. Such processing otherwise requires atomic layer deposition, at least due to the preamble limitation in each of claims 1 and 18. Accordingly, entry of this amendment is requested.

Claim 17 is amended in a manner consistent with an amendment made in the parent application. Entry of this amendment is requested.

All claims stand rejected as being obvious over various combinations of references, each of which includes U.S. Patent No. 6,461,436 to Campbell et al. However, this reference is not §103 prior art to this application. Specifically, this application claims priority to an application which was filed after November 29, 1999. Accordingly, the provisions of 35 U.S.C. §103(c) apply. The cited Campbell et al. patent is only understood to qualify as prior art under one or more of subsections (e), (f) and (g) of §102 of 35 U.S.C. This application, the priority application and the application that became the cited '436 Campbell et al. patent are assigned to Micron Technology, Inc. The undersigned hereby asserts that the subject matter that became the '436 Campbell et al. patent and the claims invention herein were, at the time the invention herein was made, owned by Micron

Technology, Inc., or subject to an obligation of assignment to Micron

Technology, Inc. Accordingly hereby, the '436 Campbell et al. is not §103

prior art to this application and, therefore, the rejection of the claims over

this reference must be withdrawn. Action to that end is requested. No

admission is made regarding the propriety of the Examiner's rejection even

where the '436 Campbell et al. patent subject matter prior art to this

application.

Dependent claims 54 and 55 are added. Such recite processing

relative to the chamber which is sized to retain no more than a single wafer

at a time for atomic layer depositing upon, and recite that the positioning is

with respect to only a single wafer. Support for the same is inherent form

Applicant's application as-filed, for example as is inherent from the

specification and with respect to a single wafer 70 depicted for deposition in

the figures. Accordingly, no new matter is added.

This application is believed to be in immediate condition for allowance,

and action to that end is requested.

Respectfully submitted,

Dated: _8-17-09

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